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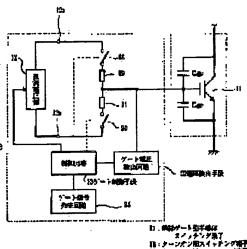
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(54) GATE DRIVE CIRCUIT FOR SEMICONDUCTOR SWITCHING ELEMENT

(57)Abstract:

PROBLEM TO BE SOLVED: To reduce a switching loss while suppressing occurrence of a current surge and a noise at a turning on time of an insulated gate type semiconductor switching element and to prolong a lifetime of the element. SOLUTION: A control circuit 23 turns on a switching element 18 for turning on an IGBT 11 when the IGBT 11 is turned on based on a gate timing signal from a gate signal generator 24, outputs an on-voltage from a first output terminal 12a of a DC voltage source 12, lowers a level of the on-voltage from the first output terminal 12a thereafter when the gate voltage of the IGBT 11 for detecting a gate voltage detector 22 arrives at a first set value and further resets the level of the on-voltage to an original state when the gate voltage to be detected by the gate voltage detector 22 arrives at a second set value (> the first set value).



LEGAL STATUS

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